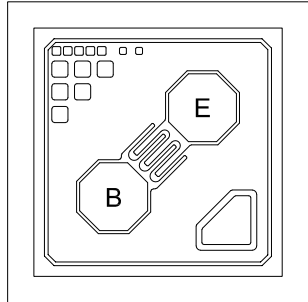


The CP617-CM4957 is a silicon PNP RF transistor designed for high frequency amplifier and non-saturated switching applications.



BACKSIDE COLLECTOR R1

MECHANICAL SPECIFICATIONS:

Die Size	15.7 x 15.7 MILS
Die Thickness	7.9 MILS
Base Bonding Pad Size	3.54 x 3.54 MILS
Emitter Bonding Pad Size	3.54 x 3.54 MILS
Top Side Metalization	Al – 9,000Å
Back Side Metalization	Au – 10,000Å
Scribe Alley Width	2.9 MILS
Wafer Diameter	4 INCHES
Gross Die Per Wafer	44,140

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Continuous Collector Current	I_C	30	mA
Continuous Base Current	I_B	2.0	A
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=10\text{V}$			100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	30			V
BV_{CEO}	$I_C=1.0\text{mA}$	25			V
BV_{EBO}	$I_E=100\mu\text{A}$	3.0			V
h_{FE}	$V_{CE}=10\text{V}, I_C=2.0\text{mA}$	20		150	
h_{fe}	$V_{CE}=10\text{V}, I_C=2.0\text{mA}, f=1.0\text{kHz}$	20		200	
C_{cb}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		1.6	2.0	pF
f_T	$V_{CE}=10\text{V}, I_C=2.0\text{mA}, f=100\text{MHz}$	1200		2500	MHz
G_{pe}	$V_{CE}=10\text{V}, I_C=4.0\text{mA}, f=450\text{MHz}$	17		25	dB

CP617-CM4957

Typical Electrical Characteristics

